



# STK28N3LLH5

N-channel 30 V, 0.0035  $\Omega$ , 28 A, PolarPAK<sup>®</sup>  
STripFET<sup>™</sup>V Power MOSFET

Preliminary Data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	R <sub>DS(on)</sub> *Q <sub>g</sub>
STK28N3LLH5	30 V	< 0.0045 $\Omega$	68.4 nC*m $\Omega$

- Ultra low top and bottom junction to case thermal resistance
- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- Very low switching gate charge
- Fully encapsulated die
- 100% matte tin finish (in compliance with the 2002/95/EC european directive)
- High avalanche ruggedness
- PolarPAK<sup>®</sup> is a trademark of VISHAY

## Application

- Switching applications

## Description

This product utilizes the 5th generation of design rules of ST's proprietary STripFET<sup>™</sup> technology. The lowest available R<sub>DS(on)</sub>\*Q<sub>g</sub>, in this chip scale package, makes this device suitable for the most demanding DC-DC converter applications, where high power density is to be achieved.

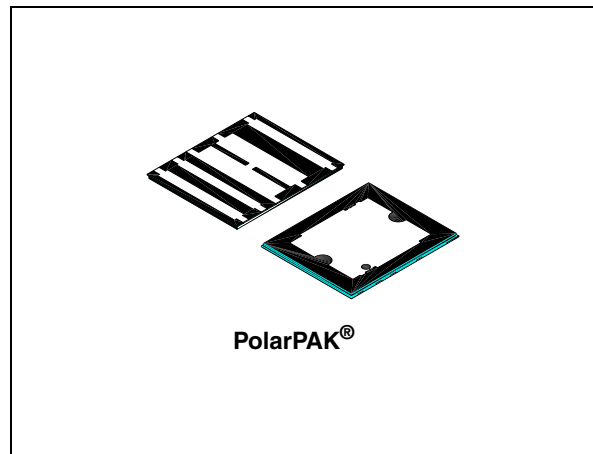


Figure 1. Internal schematic diagram

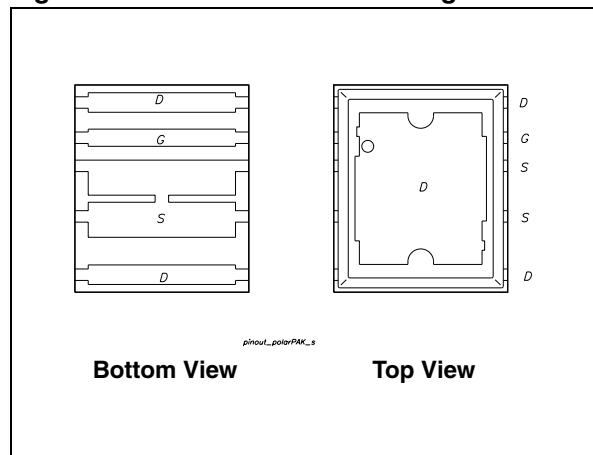


Table 1. Device summary

Order code	Marking	Package	Packaging
STK28N3LLH5	283L5	PolarPAK <sup>®</sup>	Tape and reel

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 22$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	28	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	17.5	A
$I_{DM}^{(2)}$	Drain current (pulsed)	112	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25^\circ\text{C}$	5.2	W
	Derating factor	0.0416	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	1	J
$T_j$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2 oz Cu and  $\leq 10\text{sec}$
2. Pulse width limited by package
3. Starting  $T_j = 25^\circ\text{C}$ ,  $I_D = 10\text{A}$ ,  $V_{DD} = 25\text{V}$

**Table 3. Thermal data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb	20	24	$^\circ\text{C}/\text{W}$
$R_{thj-c}^{(2)}$	Thermal resistance junction-case (top drain)	1	1.2	$^\circ\text{C}/\text{W}$
$R_{thj-c}^{(3)}$	Thermal resistance junction-case (source)	2.8	3.4	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2 oz Cu and  $\leq 10\text{sec}$
2. Steady state
3. Measured at source pin when the device is mounted on FR-4 board in steady state

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, T_c = 125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 22 V$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 14 A$ $V_{GS} = 4.5 V, I_D = 14 A$		0.0035 0.0047	0.0045 0.0055	$\Omega$ $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25 V, f = 1 \text{ MHz}, V_{GS} = 0$		2300		pF
$C_{oss}$	Output capacitance			450		pF
$C_{rss}$	Reverse transfer capacitance			61		pF
$Q_g$	Total gate charge	$V_{DD} = 15 V, I_D = 28 A$		19		nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 4.5 V$		TBD		nC
$Q_{gd}$	Gate-drain charge	(see Figure 3)		TBD		nC
$Q_{gs1}$	Pre $V_{th}$ gate-to-source charge	$V_{DD} = 15 V, I_D = 28 A$		TBD		nC
$Q_{gs2}$	Post $V_{th}$ gate-to-source charge	$V_{GS} = 4.5 V$ (see Figure 8)		TBD		nC
$R_G$	Gate input resistance	$f = 1 \text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain		TBD		$\Omega$

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD}=15\text{ V}$ , $I_D=14\text{ A}$ , $R_G=4.7\ \Omega$ , $V_{GS}=4.5\text{ V}$ (see Figure 2)		TBD TBD		ns ns
$t_{d(off)}$ $t_f$	Turn-off delay time Fall time	$V_{DD}=15\text{ V}$ , $I_D=14\text{ A}$ , $R_G=4.7\ \Omega$ , $V_{GS}=4.5\text{ V}$ (see Figure 2)		TBD TBD		ns ns

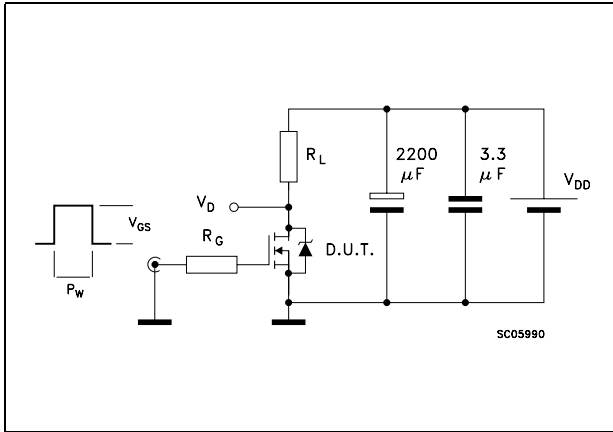
**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				28 112	A A
$V_{SD}^{(2)}$	Forward on Voltage	$I_{SD}=25\text{ A}$ , $V_{GS}=0$			1.1	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=25\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=20\text{ V}$ , $T_j=150^\circ\text{C}$ (see Figure 7)		TBD TBD TBD		ns nC A

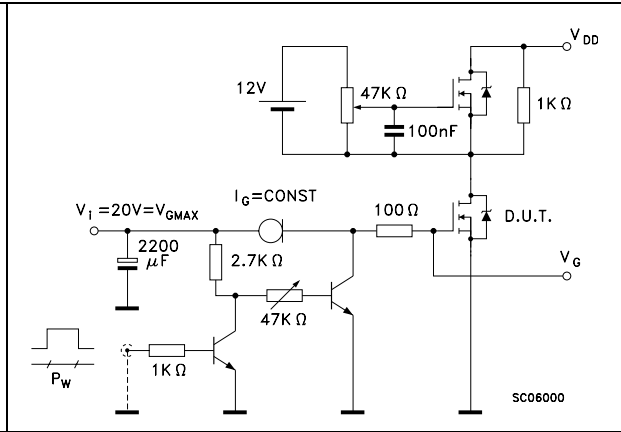
1. Pulse width limited by package
2. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

### 3 Test circuits

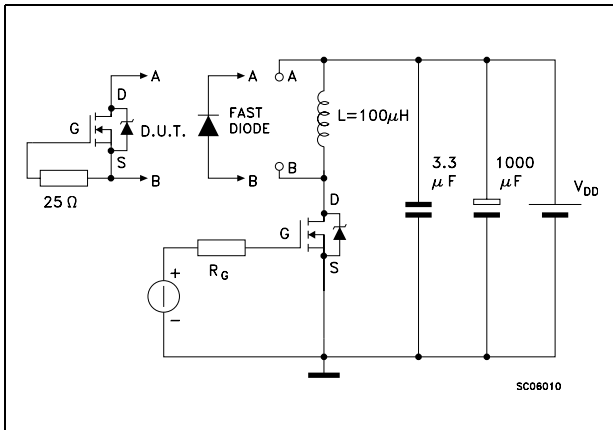
**Figure 2. Switching times test circuit for resistive load**



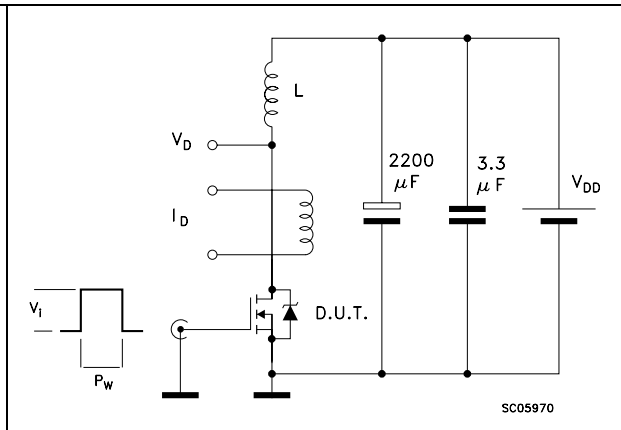
**Figure 3. Gate charge test circuit**



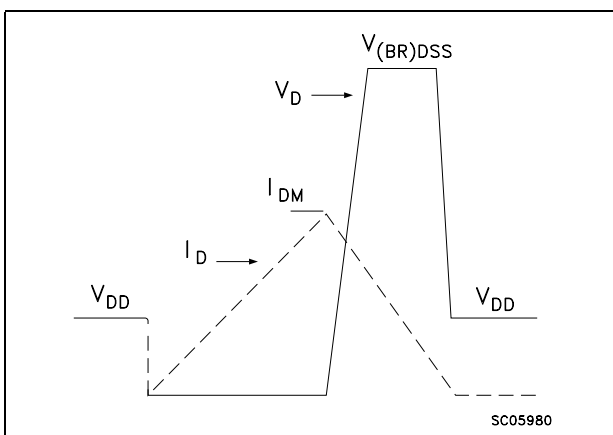
**Figure 4. Test circuit for inductive load switching and diode recovery times**



**Figure 5. Unclamped inductive load test circuit**



**Figure 6. Unclamped inductive waveform**



**Figure 7. Switching time waveform**

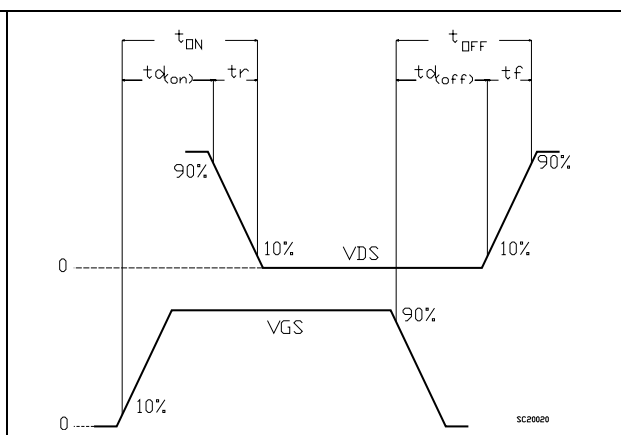
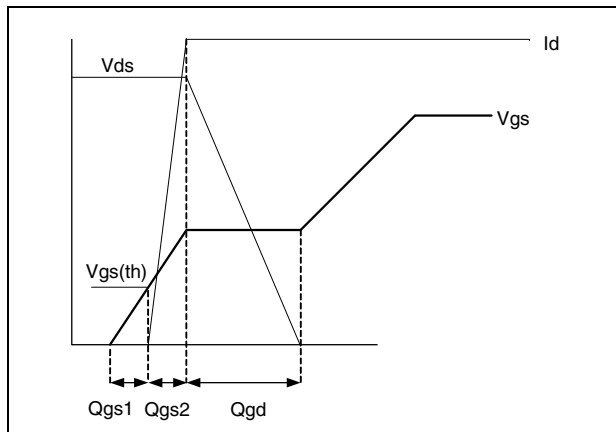


Figure 8. Gate charge waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)



Table 8. PolarPAK® (option “S”) mechanical data

Ref.	mm			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.75	0.80	0.85	0.030	0.031	0.033
A1			0.05			0.002
b1	0.48	0.58	0.68	0.019	0.023	0.027
b2	0.41	0.51	0.61	0.016	0.020	0.024
b3	2.19	2.29	2.39	0.086	0.090	0.094
b4	0.89	1.04	1.19	0.035	0.041	0.047
b5	0.23	0.33	0.43	0.009	0.013	0.017
c	0.20	0.25	0.30	0.008	0.010	0.012
D	6	6.15	6.30	0.236	0.242	0.248
D1	5.74	5.89	6.04	0.226	0.232	0.238
E	5.01	5.16	5.31	0.197	0.203	0.209
E1	4.75	4.90	5.05	0.187	0.193	0.199
H1	0.23			0.009		
H2	0.45		0.56	0.018		0.022
H3	0.31	0.41	0.51	0.012	0.016	0.020
H4	0.45		0.56	0.018		0.022
I1	1.92	1.97	2.02	0.075	0.077	0.079
J1	0.38	0.43	0.48	0.014	0.016	0.018
K1	4.22	4.37	4.52	0.166	0.172	0.178
K4	0.24			0.009		
M1	4.30	4.50	4.70	0.169	0.177	0.185
M2	3.43	3.58	3.73	0.135	0.141	0.147
M3	0.22			0.009		
M4	0.05			0.002		
P1	0.15	0.20	0.25	0.006	0.008	0.010
T1	3.48	3.64	4.10	0.137	0.143	0.161
T2	0.56	0.76	0.95	0.022	0.030	0.037
T3	1.20			0.047		
T4	3.90			0.154		
T5		0.18	0.36		0.007	0.014
<	0°	10°	12°	0°	10°	12°

Figure 9. PolarPAK® (option “S”) drawings

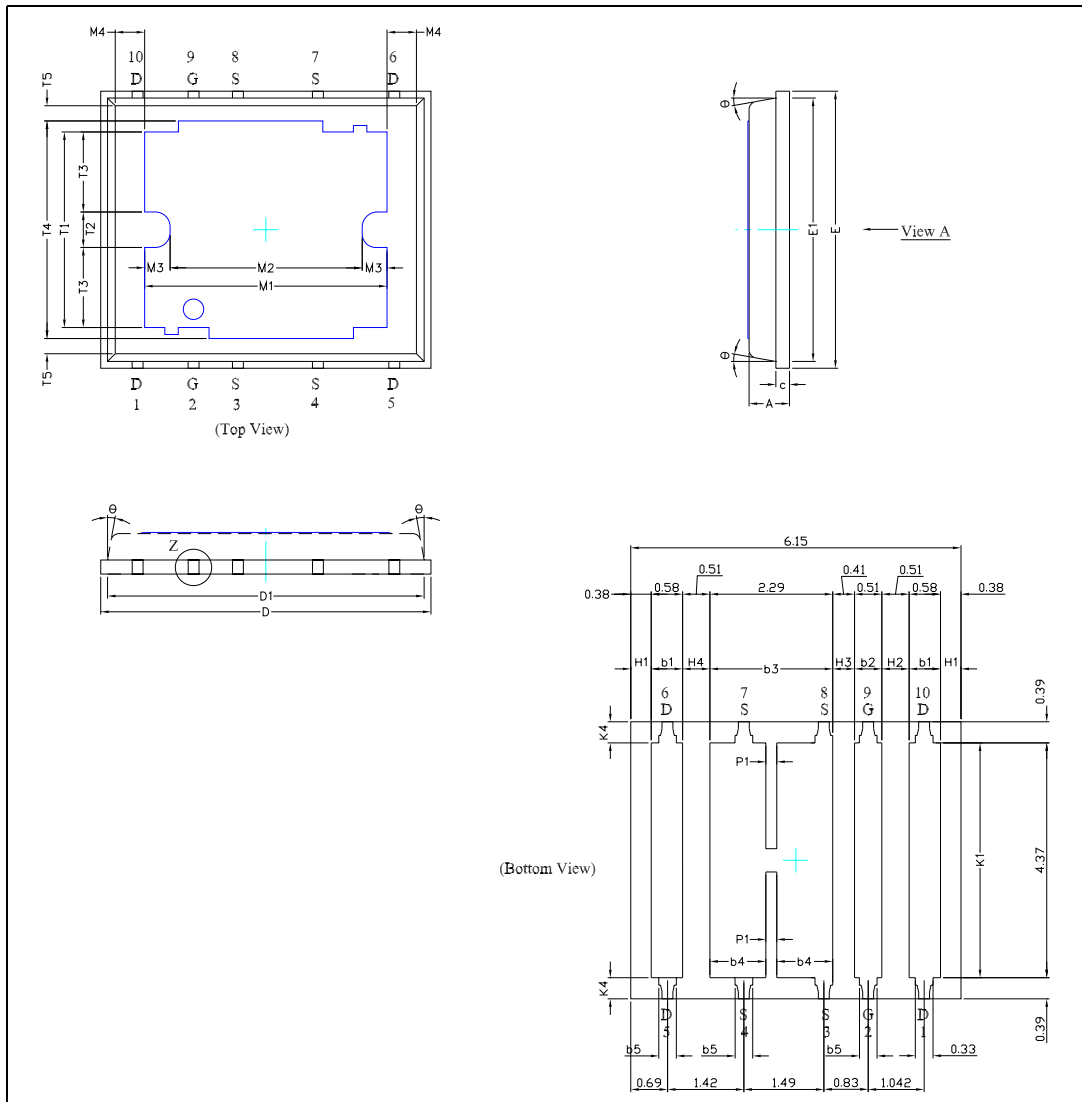
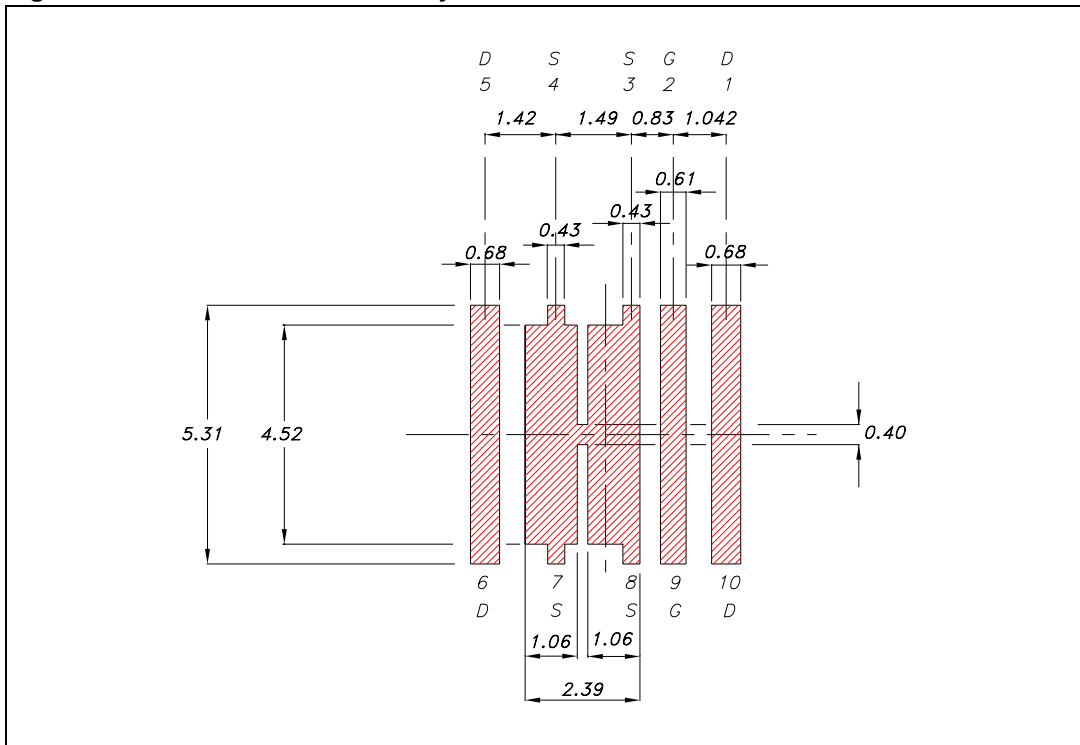


Figure 10. Recommended PAD layout



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
07-Jul-2008	1	First release
03-Sep-2008	2	R <sub>DS(on)</sub> value updated. V <sub>GS</sub> value updated in <a href="#">Table 2</a> and <a href="#">Table 4</a>

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